

Abstracts

A 3.2-V operation single-chip AlGaAs/GaAs HBT MMIC power amplifier for GSM900/1800 dual-band applications

K. Yamamoto, T. Shimura, T. Asada, T. Okuda, K. Mori, K. Choumei, S. Suzuki, T. Miura, S. Fujimoto, R. Hattori, H. Nakano, K. Hosogi, J. Otsuji, A. Inoue, K. Yajima, T. Ogata, Y. Mijazaki and M. Yamanouchi. "A 3.2-V operation single-chip AlGaAs/GaAs HBT MMIC power amplifier for GSM900/1800 dual-band applications." 1999 MTT-S International Microwave Symposium Digest 99.4 (1999 Vol. IV [MWSYM]): 1397-1400 vol.4.

A 3.2-V operation single-chip HBT MMIC power amplifier has been successfully developed for GSM900/1800 applications, featuring on-chip bias circuits switched in turn between 900 MHz and 1800 MHz. The IC delivers a P/sub out/ of over 34.5 dBm and a PAE of over 50% for GSM900, a 32-dBm P/sub out/ and a 42% PAE for GSM1800 (DCS 1800).

 [Return to main document.](#)